



**Shantou Huashan Electronic Devices Co.,Ltd.**

NPN SILICON TRANSIST OR

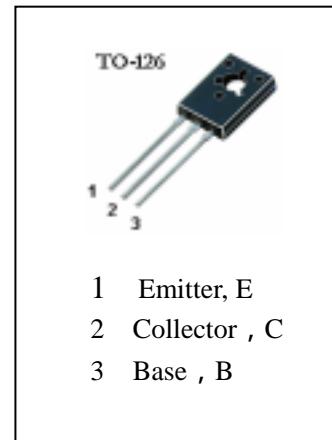
**HSBD139**

## APPLICATIONS

Medium Power Linear switching Applications

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_c$ —Collector Dissipation ( $T_c=25^\circ C$ ) .....	12.5W
$P_c$ —Collector Dissipation ( $T_A=25^\circ C$ ) .....	1.25W
$V_{CBO}$ —Collector-Base Voltage.....	80V
$V_{CEO}$ —Collector-Emitter Voltage.....	80V
$V_{EBO}$ —Emitter-Base Voltage.....	5V
$I_c$ —Collector Current( Pulse ).....	3A
$I_c$ —Collector Current ( DC ) .....	1.5A
$I_b$ —Base Current.....	0.5A



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$I_{CBO}$	Collector Cut-off Current			0.1	$\mu A$	$V_{CB}=30V, I_E=0$
$I_{EBO}$	Emitter-Base Cut-off Current			10	$\mu A$	$V_{EB}=5V, I_C=0$
$h_{FE(1)}$	DC Current Gain	25				$V_{CE}=2V, I_C=5mA$
$h_{FE(2)}$		25				$V_{CE}=2V, I_C=0.5A$
$h_{FE(3)}$		40		250		$V_{CE}=2V, I_C=150mA$
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage			0.5	V	$I_C=500mA, I_B=50mA$
$V_{BE(ON)}$	Base-Emitter On Voltage			1.0	V	$I_C=0.5A, V_{CE}=2V$
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	80				$I_C=30mA, I_B=0$

### $h_{FE(3)}$ Classification

Classification	6	10	16
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$h_{FE(3)}$	40~100	63~160	100~250
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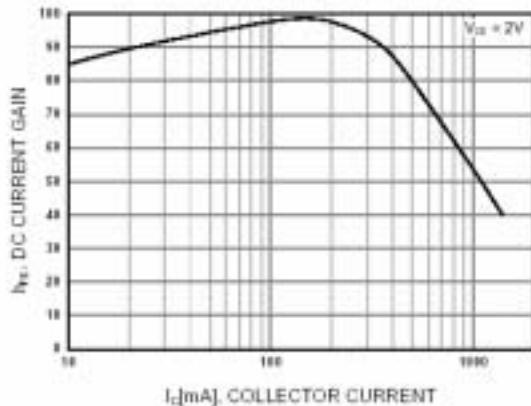


Figure 1. DC current Gain

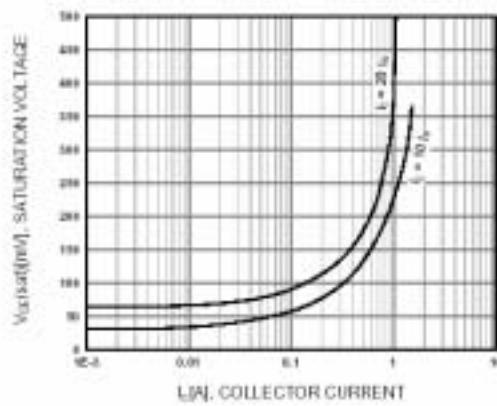


Figure 2. Collector-Emitter Saturation Voltage

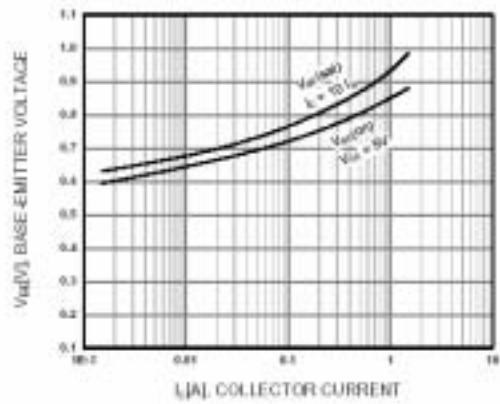


Figure 3. Base-Emitter Voltage

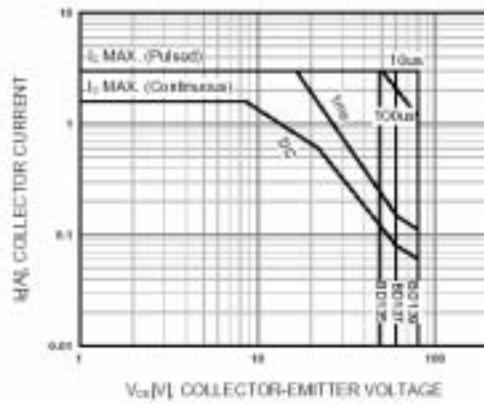


Figure 4. Safe Operating Area

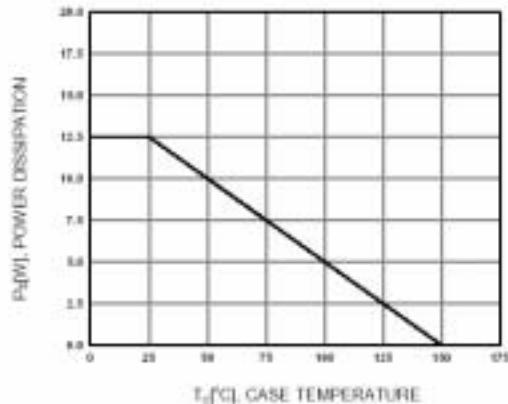


Figure 5. Power Derating